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customized optoelectronics



Product Data Sheet

LED Chip ultraviolet

EOLC-430-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
UV		P + N up

	<p>Description</p> <ul style="list-style-type: none"> -Substrate: Sapphire, epitaxial layer: GaN based Material -N bonding pad electrode: Au alloy -P bonding pad electrode: Au alloy
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Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20\text{mA}$	V_F		3.5	3.8	V
Reverse current	$V_R = 5\text{V}$	I_R			1	μA
Peak wavelength	$I_F = 20\text{mA}$	λ_p	430		435	nm
Full width at half maximum	$I_F = 20\text{mA}$	$\Delta\lambda$		30		nm
Luminous intensity ¹	$I_F = 20\text{mA}$	I_v	4		6	mW

Packing

Chips on adhesive film with wire-bond side top

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.